

Fakultät 1
Institut für Physik

Invitation to Physics Colloquium

Lecturer:

***Prof. Dr. Johannes Heitmann
TU Bergakademie Freiberg***

Topic:

***"Atomic Layer Processing for Performance Improvement of High
Power Nitride Devices"***

Nitride devices e.g. AlGaN/GaN heterostructures are one of the main candidates for current power electronics and RF applications [1,2]. To improve device performance materials with either higher spontaneous polarization fields to increase carrier density in the two-dimensional electron gas (2DEG) formed at the heterointerface, or with a higher band gap like AlN are investigated [3, 4]. In both cases, the ohmic contact formation to the 2DEG is demanding and for the shrinking dimensions the contact resistance of source and drain becomes crucial for the resulting ON-resistance.

Date: Thursday, 15.01.2025

Time: 03:30 p.m.

Location: ZHG, room SR1

Im Auftrag von Prof. Flege - Stefanie Jannasch

FG Angewandte Physik und Halbleiterspektroskopie

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